



SP 09/945554

PATENTIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes
Serial No.: 09/945554
Filed: August 30, 2001
Title: SRAM CELLS WITH REPRESSED FLOATING GATE MEMORY, LOW
TUNNEL BARRIER INTERPOLY INSULATORS

Examiner: Thomas L Dickey
Group Art Unit: 2826
Docket: 1303.028US1

INFORMATION DISCLOSURE STATEMENT

Mail Stop RCE
Assistant Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. § 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. § 1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES

By his Representatives,

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29 July '03

By

Timothy B Clise
Reg. No. 40,957

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner of Patents, P.O.Box 1450, Alexandria, VA 22313-1450, on this 29th day of July, 2003.

Name

Amy Moriarty

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

Complete if Known

Application Number	09/945554
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Dickey, Thomas

Attorney Docket No: 1303.028US1

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US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US-5,952,692	09/14/1999	Nakazato, K. , et al.	257	321	10/28/1997
	US-6,210,999	04/03/2001	Gardner, , et al.	438	183	12/04/1998
	US-6,475,857	11/05/2002	Kim, W. , et al.	438	240	06/21/2001
	US-6,541,280	04/01/2003	Kaushik, , et al.			03/20/2001

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		AARIK, JAAN , et al., "Anomalous effect of temperature on atomic layer deposition of titanium oxide", <u>Journal of Crystal Growth</u> , (2000),pp. 531-537	
		AARIK, JAAN , et al., "Texture development in nanocrystalline hafnium dioxide thin films grown by atomic layer deposition", <u>Journal of Crystal Growth</u> , (2000),pp. 105-113	
		FERGUSON, J D., et al., "Atomic layer deposition of Al ₂ O ₃ and SiO ₂ on BN particles using sequential surface reaction", <u>Applied Surface Science</u> , (2000),pp. 280-292	
		KIM, YONG S., et al., "Effect of rapid thermal annealing on the structure and the electrical properties of atomic-layer-deposited Ta ₂ O ₅ films", <u>Journal of the Korean Physical Society</u> , (December 2000),pp. 975-979	
		KIM, YEONG K., et al., "Novel capacitor technology for high density stand-alone and embedded DRAMs", <u>IEEE</u> , (2000),4 pages	
		KUKLI, KAUPÖ , "Atomic Layer Deposition of Titanium Oxide from TiI ₄ and H ₂ O ₂ ", <u>Chemical Vapor Deposition</u> , (2000),pp. 303-310	
		KUKLI, KAUPÖ , et al., "Atomic layer deposition of zirconium oxide from zirconium tetraiodide, water and hydrogen peroxide", <u>Journal of Crystal Growth</u> , (2001),pp. 262-272	
		KUKLI, KAUPÖ , et al., "Real-time monitoring in atomic layer deposition of TiO ₂ from TiI ₄ and H ₂ O-H ₂ O ₂ ", <u>American Chemical Society</u> , (2000),pp. 8122-8128	
		LEE, J. , "Effect of Polysilicon Gate on the Flatband Voltage Shift and Mobility Degradation for ALD-Al ₂ O ₃ Gate Dielectric", <u>IEDM</u> , (2000),pp. 645-648	
		PARANJPE, AJIT , et al., "Atomic layer deposition of AlO _x for thin film head gap application", <u>Journal of the Electrochemical Society</u> , (September 2001),pp. 465-471	

EXAMINER**DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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Application Number	09/945554
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First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Dickey, Thomas

Attorney Docket No: 1303.028US1

Sheet 2 of 2

SMITH, RYAN C., et al., "Chemical vapour deposition of the oxides of titanium, zirconium and hafnium for use as high-k materials in microelectronic devices. A carbon-free precursor for the synthesis of hafnium dioxide", <u>Advanced Materials for Optics and Electronics</u> , (2000), 2 pages
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EXAMINER

DATE CONSIDERED

Substitute Disclosure Statement Form (PTO-1448)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached